Abstract

An interconnector line of thin film comprising 0.001 to 30 at % of at least one kind of a first element capable of constituting an intermetallic compound of aluminum and/or having a higher standard electrode potential than aluminum, for example, at least one kind of the first element selected from Y, Sc, La, Ce, Nd, Sm, Gd, Tb, Dy, Er, Th, Sr, Ti, Zr, V, Nb, Ta, Cr, Mo, W, Mn, Tc, Re, Fe, Co, Ni, Pd, Ir, Pt, Cu, Ag, Au, Cd, Si, Pb and B; and one kind of a second element selected from C, O, N and H in a proportion of 0.01 at ppm to 50 at % of the first element, with the balance comprising substantially Al. In addition to having low resistance, such an Al interconnector line of thin film can prevent the occurrence of hillocks and the electrochemical reaction with an ITO electrode. The interconnector line of thin film can be obtained by sputtering in a dust-free manner by using a sputter target having a similar composition.